

Dual SCHOTTKY Barrier Diodes

Application circuit designs are moving toward the consolidation of device count and into smaller packages. The new SOT-363 package is a solution which simplifies circuit design, reduces device count, and reduces board space by putting two discrete devices in one small six-leaded package. The SOT-363 is ideal for low-power surface mount applications where board space is at a premium, such as portable products.

Surface Mount Comparisons:

	SOT-363	SOT-23
Area (mm ²)	4.6	7.6
Max Package P _D (mW)	120	225
Device Count	2	1

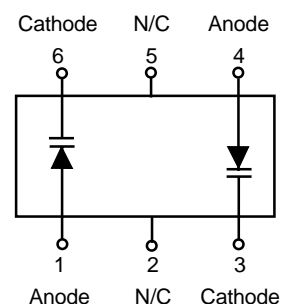
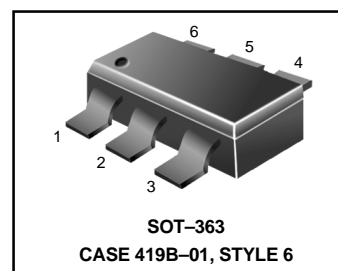
Space Savings:

Package	1 x SOT-23	2 x SOT-23
SOT-363	40%	70%

The MBD110DW, MBD330DW, and MBD770DW devices are spin-offs of our popular MMBD101LT1, MMBD301LT1, and MMBD701LT1 SOT-23 devices. They are designed for high-efficiency UHF and VHF detector applications. Readily available to many other fast switching RF and digital applications.

- Extremely Low Minority Carrier Lifetime
- Very Low Capacitance
- Low Reverse Leakage

MBD110DWT1
MBD330DWT1
MBD770DWT1



MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Reverse Voltage	MBD110DWT1	V _R	7.0 Vdc
	MBD330DWT1		30
	MBD770DWT1		70
Forward Power Dissipation T _A = 25°C	P _F	120	mW
Junction Temperature	T _J	-55 to +125	°C
Storage Temperature Range	T _{stg}	-55 to +150	°C

DEVICE MARKING

MBD110DWT1 = M4 MBD330DWT1 = T4 MBD770DWT1 = H5

Thermal Clad is a trademark of the Bergquist Company.

MBD110DWT1 MBD330DWT1 MBD770DWT1

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic		Symbol	Min	Typ	Max	Unit
Reverse Breakdown Voltage (I _R = 10 μA)	MBD110DWT1 MBD330DWT1 MBD770DWT1	V _{(BR)R}	7.0 30 70	10 — —	— — —	Volts
Diode Capacitance (V _R = 0, f = 1.0 MHz, Note 1)	MBD110DWT1	C _T	—	0.88	1.0	pF
Total Capacitance (V _R = 15 Volts, f = 1.0 MHz)	MBD330DWT1	C _T	—	0.9	1.5	pF
(V _R = 20 Volts, f = 1.0 MHz)	MBD770DWT1		—	0.5	1.0	
Reverse Leakage (V _R = 3.0 V)	MBD110DWT1	I _R	—	0.02	0.25	μA
(V _R = 25 V)	MBD330DWT1		—	13	200	nAdc
(V _R = 35 V)	MBD770DWT1		—	9.0	200	nAdc
Noise Figure (f = 1.0 GHz, Note 2)	MBD110DWT1	NF	—	6.0	—	dB
Forward Voltage (I _F = 10 mA)	MBD110DWT1	V _F	—	0.5	0.6	Vdc
(I _F = 1.0 mAdc)	MBD330DWT1		—	0.38	0.45	
(I _F = 10 mA)			—	0.52	0.6	
(I _F = 1.0 mAdc)	MBD770DWT1		—	0.42	0.5	
(I _F = 10 mA)			—	0.7	1.0	

MBD110DWT1 MBD330DWT1 MBD770DWT1

TYPICAL CHARACTERISTICS — MBD110DWT1

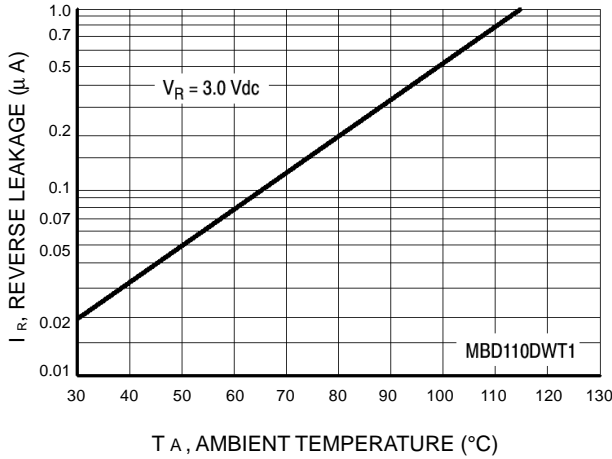


Figure 1. Reverse Leakage

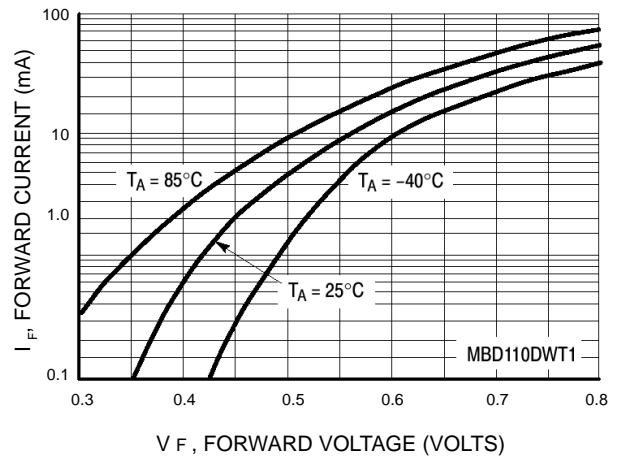


Figure 2. Forward Voltage

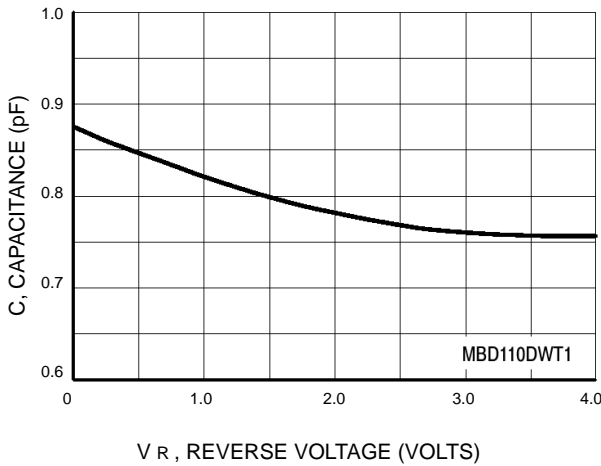


Figure 3. Capacitance

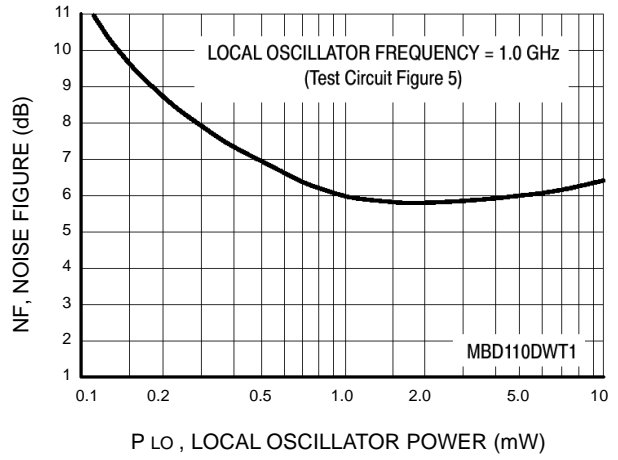


Figure 4. Noise Figure

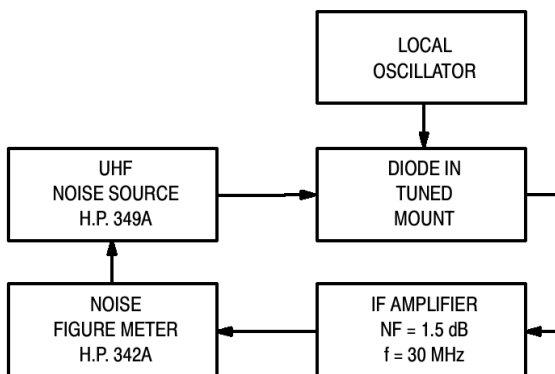


Figure 5. Noise Figure Test Circuit

NOTES ON TESTING AND SPECIFICATIONS

Note 1 – C_C and C_T are measured using a capacitance bridge (Boonton Electronics Model 75A or equivalent).

Note 2 – Noise figure measured with diode under test in tuned diode mount using UHF noise source and local oscillator (LO) frequency of 1.0 GHz. The LO power is adjusted for 1.0 mW. I_F amplifier NF = 1.5 dB, $f = 30$ MHz, see Figure 5.

Note 3 – L_S is measured on a package having a short instead of a die, using an impedance bridge (Boonton Radio Model 250A RX Meter).

MBD110DWT1 MBD330DWT1 MBD770DWT1

TYPICAL CHARACTERISTICS MBD330DWT1

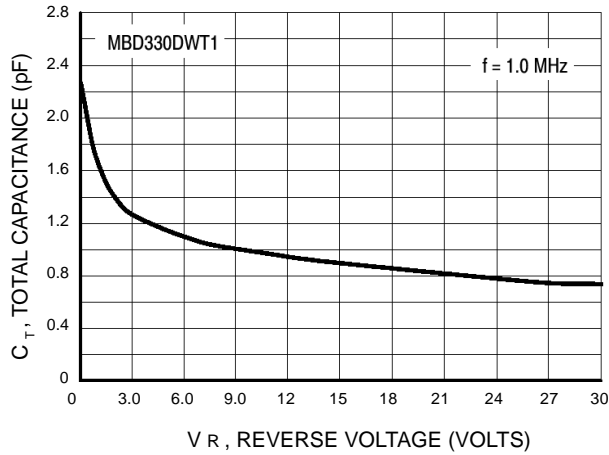


Figure 6. Total Capacitance

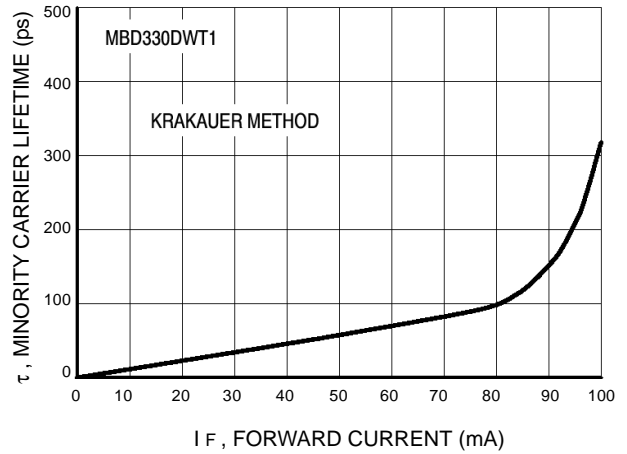


Figure 7. Minority Carrier Lifetime

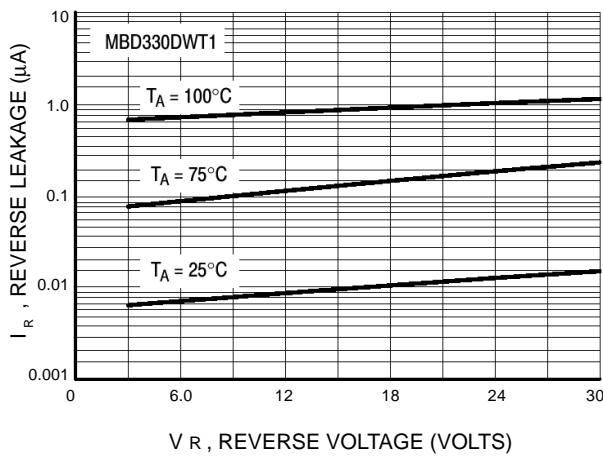


Figure 8. Reverse Leakage

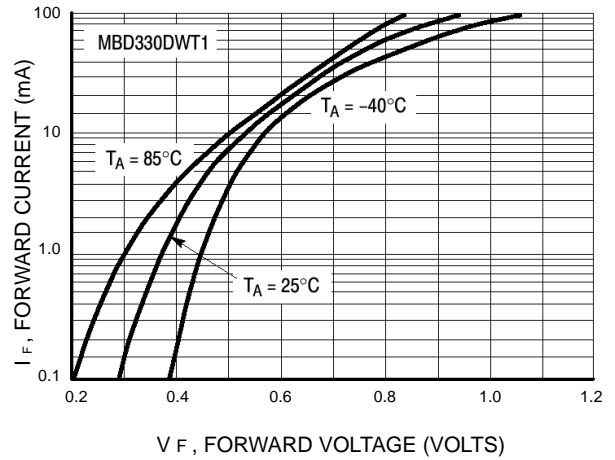


Figure 9. Forward Voltage

MBD110DWT1 MBD330DWT1 MBD770DWT1

TYPICAL CHARACTERISTICS MBD770DWT1

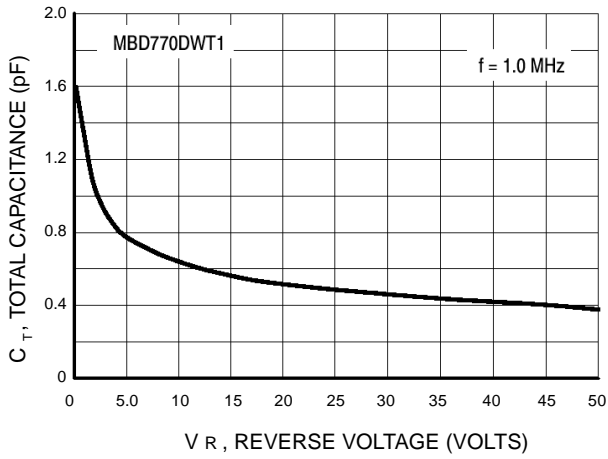


Figure 10 . Total Capacitance

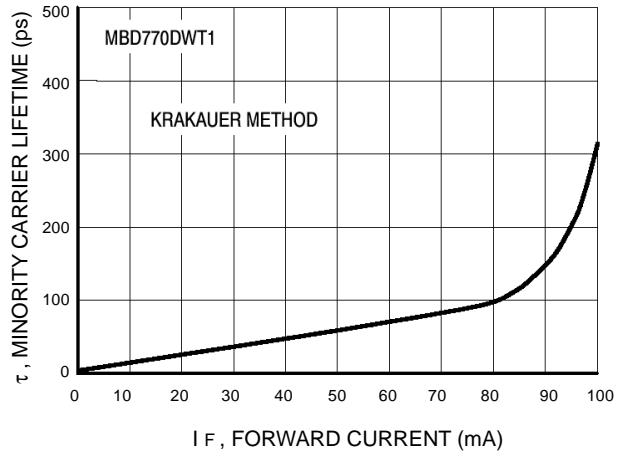


Figure 11. Minority Carrier Lifetime

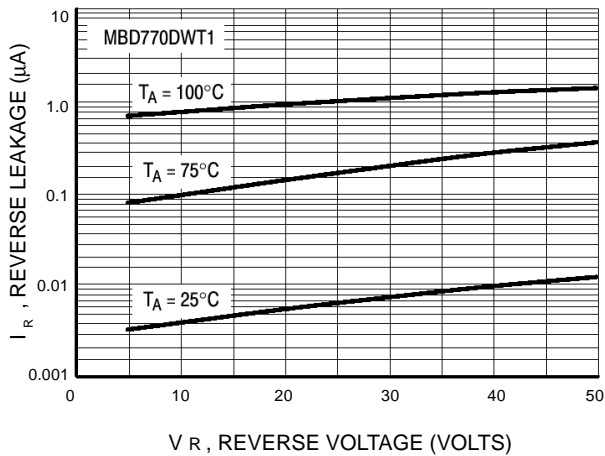


Figure 12. Reverse Leakage

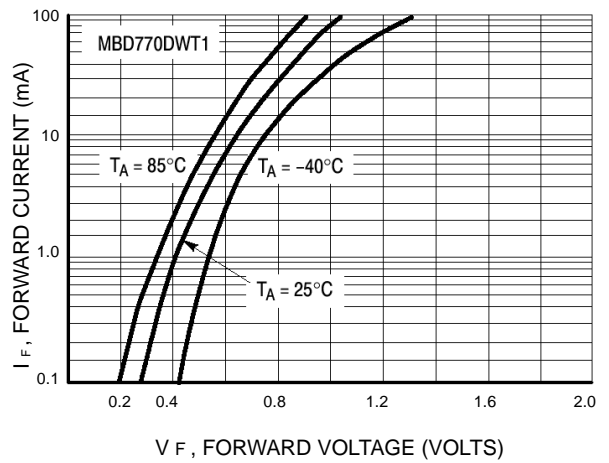


Figure 13. Forward Voltage